





DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead Free/RoHS Compliant (Note 1)
- "Green" Device (Notes 2 and 3)

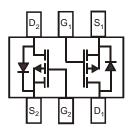
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)

SOT363



Top View



Top View Internal Schematic

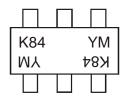
Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
BSS84DW-7-F	Commercial	SOT363	3,000/Tape & Reel
BSS84DWQ-13	Automotive	SOT363	10,000/Tape & Reel
BSS84DWQ-7	Automotive	SOT363	3,000/Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



K84 = Product Type Marking Code YM = Date Code Marking

Y = Year (ex: N = 2002) M = Month (ex: 9 = September)

Date Code Key	/														
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Х	Υ	Z
Month	Jan	Fe	b	Mar	Apr	Мау	Ju	n	Jul	Aug	Sep	Ос	t	Nov	Dec
Codo	4	2		2	4	E	6		7	0	0			NI	_



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-50	V
Drain-Gate Voltage (Note 5)		V_{DGR}	-50	V
Gate-Source Voltage	Continuous	V_{GSS}	±20	V
Drain Current (Note 6)	Continuous	I _D	-130	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units		
Total Power Dissipation (Note 6)	P_{D}	300	mW		
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	417	°C/W		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	Syllibol	IAIIII	тур	IVIAA	Offic	rest Condition
, ,						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	-75	—	V	$V_{GS} = 0V, I_D = -250\mu A$
		_	_	-15	μΑ	$V_{DS} = -50V$, $V_{GS} = 0V$, $T_{J} = 25$ °C
Zero Gate Voltage Drain Current	Inno		_	-60	μA	$V_{DS} = -50V$, $V_{GS} = 0V$, $T_{J} = 125$ °C
2010 Gate Voltage Brain Guneric	IDSS	_	_	-100	nA	$V_{DS} = -25V$, $V_{GS} = 0V$, $T_{J} = 25^{\circ}C$
Gate-Body Leakage	I _{GSS}		_	±10	nΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.8	-1.6	-2.0	V	$V_{DS} = V_{GS}$, $I_D = -1mA$
Static Drain-Source On-Resistance	R _{DS} (ON)	_	6	10	Ω	$V_{GS} = -5V, I_D = -0.100A$
Forward Transconductance	g _{FS}	0.05	_	_	S	$V_{DS} = -25V, I_{D} = -0.1A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	_	_	45	pF	
Output Capacitance	Coss	_	_	25	pF	$V_{DS} = -25V$, $V_{GS} = 0V$, $f = 1.0MHz$
Reverse Transfer Capacitance	C _{rss}	_	_	12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	_	10	_	ns	$V_{DD} = -30V$, $I_D = -0.27A$,
Turn-Off Delay Time	t _{D(OFF)}	_	18	_	ns	$R_{GEN} = 50\Omega$, $V_{GS} = -10V$

Notes: 5. R

^{5.} $R_{GS} \le 20 K\Omega$.

^{6.} Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.

^{7.} Short duration pulse test used to minimize self-heating effect.



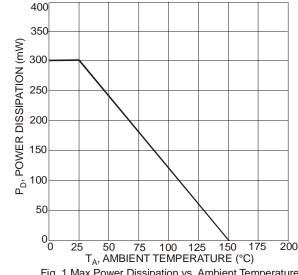
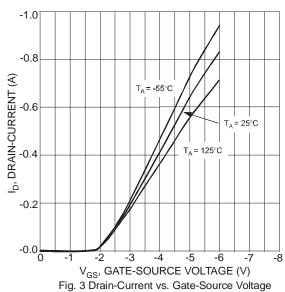
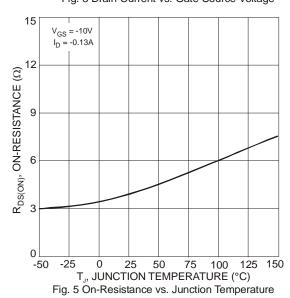


Fig. 1 Max Power Dissipation vs. Ambient Temperature





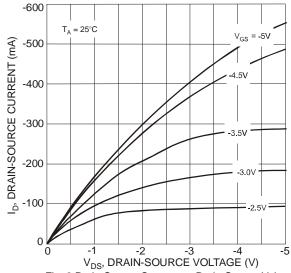


Fig. 2 Drain-Source Current vs. Drain-Source Voltage

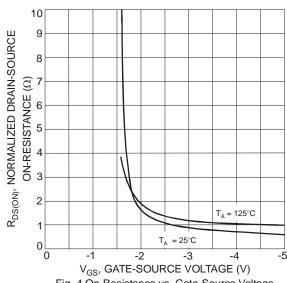


Fig. 4 On-Resistance vs. Gate-Source Voltage

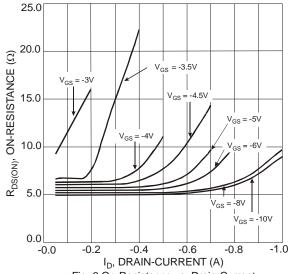
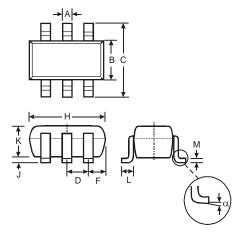


Fig. 6 On-Resistance vs. Drain-Current

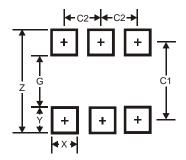


Package Outline Dimensions



SOT363							
Dim	Min	Max					
Α	0.10	0.30					
В	1.15	1.35					
С	2.00	2.20					
D	0.65	Тур					
F	0.40	0.45					
Н	1.80	2.20					
7	0	0.10					
K	0.90	1.00					
L	L 0.25						
М	0.10	0.22					
α	0°	8°					
All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65



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